## NSN 5961-01-352-3480



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-352-3480 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** Between 0.250 inches and 0.360 inches Overall Width: 1.050 inches **End Application:** Satellite communications terminal an/usc-38 (v)1 **Mounting Facility Quantity: Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case and electrostatic sensitive **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 drain to gate voltage and 100.0 drain to source voltage and 20.0 gate to source voltage **Current Rating Per Characteristic:** 56.00 amperes off-state current, peak **Power Rating Per Characteristic:** 75.0 watts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Special Features:** Nuclear hardness critical item **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:** 

**Demilitarization:** No

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